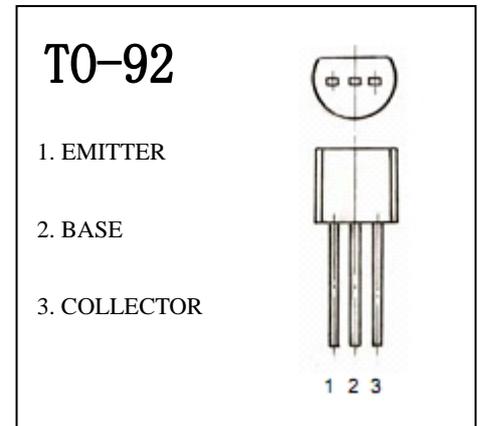




**KSP94 TRANSISTOR(PNP)**

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	-400	V
VCEO	Collector-Emitter Voltage	-400	V
VEBO	Emitter-Base Voltage	-6	V
IC	Collector Current	-0.3	A
PC	Collector Power Dissipation	625	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=-100uA, IE=0	-400			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=-1mA, IB=0	-400			V
Emitter-base breakdown voltage	V(BR)EBO	IC=-100uA, IC=0	-6			V
Collector cut-off current	ICBO	VCB=-300V, IE=0			-0.1	μA
Emitter cut-off current	IEBO	VEB=-4V, IC=0			-0.1	μA
DC current gain	HFE	Vce=-10V, IC=-1mA	40		300	
Collector-emitter saturation voltage	VCE(sat)	IC=-10mA, IB=-1mA			-0.5	V
Base-emitter saturation voltage	VBE(sat)	IC=-10mA, IB=-1mA			-0.75	V
Collector output capacitance	Cob	VCB=-20V, IE=0, f=1MHz			7	pF